

(12) 按照专利合作条约所公布的国际申请

(19) 世界知识产权组织
国际局

(43) 国际公布日
2022 年 3 月 3 日 (03.03.2022)



(10) 国际公布号
WO 2022/042471 A1

(51) 国际专利分类号:
H01L 21/67 (2006.01)

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(21) 国际申请号: PCT/CN2021/114024

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(22) 国际申请日: 2021 年 8 月 23 日 (23.08.2021)

(25) 申请语言: 中文

(26) 公布语言: 中文

(30) 优先权:
202010862303.X 2020 年 8 月 25 日 (25.08.2020) CN

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(81) 指定国 (除另有指明, 要求每一种可提供的国家保护): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB,

(54) Title: HEATER AND HEATING BASE

(54) 发明名称: 加热器和加热基座

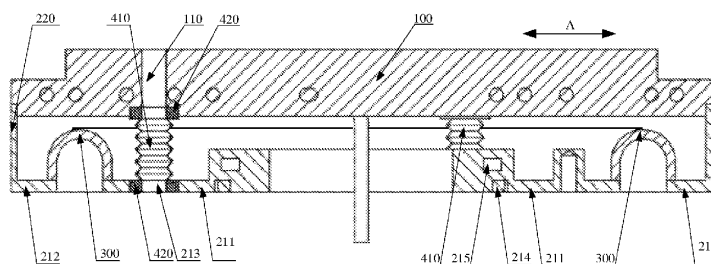


图 1

(57) Abstract: Disclosed in the present invention are a heater and a heating base. The heater is applied to a semiconductor process device, and comprises a heating body and a base used for supporting the heating body. The base comprises a base body and a vertical plate connected to each other. The base body and the heating body are arranged opposite at intervals. The vertical plate is located between the base body and the heating body, and is fixedly connected to the heating body. At least one of the vertical plate, the base body, and a joint between the vertical plate and the base body is provided with an elastic bending structure. The elastic bending structure is used for keeping connection between the vertical plate and the heating body by producing elastic deformation when the vertical plate and/or the base body expands and deforms. By means of the technical solution above, the problem of poor overall structural strength of the heater caused by the fact that at present, the expanded and deformed vertical plate is prone to failure in connection to a heating plate.

(57) 摘要: 本发明公开一种加热器和加热基座, 加热器用于半导体工艺设备, 包括加热主体和用于支撑所述加热主体的底座, 所述底座包括相互连接的座本体和立板, 所述座本体与所述加热主体相对且间隔设置, 所述立板位于所述座本体与所述加热主体之间, 且与所述加热主体固定连接, 所述立板、所述座本体和所述立板与所述座本体的连接处中的至少一者设置有弹性折弯结构, 所述弹性折弯结构用于在所述立板和/或所述座本体发生膨胀变形时, 通过产生弹性形变来使所述立板与所述加热主体保持连接。采用上述技术方案可以解决目前膨胀变形后的立板容易出现与加热盘连接失效的情况, 导致加热器的整体结构强度较差的问题。

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GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW。

(84) 指定国 (除另有指明, 要求每一种可提供的地区保护): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), 欧亚 (AM, AZ, BY, KG, KZ, RU, TJ, TM), 欧洲 (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG)。

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